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L Number	Hits	Search Text	DB	Time stamp
- Number	116	(nitride adj3 tunnel\$3) with layer	USPAT; US-PGPUB;	2002/11/26 17:23
			EPO; JPO; DERWENT; IBM_TDB	17.23
_	25	((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/22 16:40
_	3	(((nitride adj3 tunnel\$3) with layer) and (hot adj3 electron)) and (charge adj3 trap\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/22 16:44
-	854	(first adj3 voltage) and (substrate adj3 ground)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/22 16:45
_	161	((first adj3 voltage) and (substrate adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/08/22 16:46
_	. 5	, (((first adj3 voltage) and (substrate	DERWENT; IBM_TDB USPAT;	2002/08/26
	:	adj3 ground)) and (second adj3 voltage) and (ground\$3 adj3 source)) and ((hot adj3 electron) with channel) and (inject\$3 same (charge with trap\$3))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	01:19
_	1756	SONOS	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/26 01:20
_	7	SONOS and (nitride adj2 tunnel\$4)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/26 01:21
-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/26 01:26
-	7	(SONOS and (nitride adj2 tunnel\$4)) and (charge trap\$4 (first adj2 voltage) (second adj2 voltage) (first adj2 bias) (second adj2 bias) positive ground gate	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/26 01:27
_	0	substrate drain) (drain with (positive adj2 (voltage bias))) and (gate with (positive adj2 (voltage bias))) and (subtrate with ground\$3) and (source with gound\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/26 17:45
_	58434	eras\$3 and memory	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/26 17:27
-	1	(eras\$3 and memory) and (nitride adj2 tunneling adj2 layer) and (charge near2 trap\$4)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 17:28

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tunneling adj2 layer)	-	17	(eras\$3 and memory) and (nitride adj2	USPAT;	2002/11/26
Company Comp				US-PGPUB;	17:29
			June 10 - 10 - 10 - 10 - 10 - 10 - 10 - 10	EPO; JPO;	
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- 354 (((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3) ((((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (source near3 ground\$3)) and				DERWENT;	1
- 354 (((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3) ((((drain near4 (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (substrate with ground\$3)) and (gate with (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (gate with (positive adj2 (voltage potential bias))) and (source near3 ground\$3)) and (substrate with ground\$3)) and (substr				IBM_TDB	
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